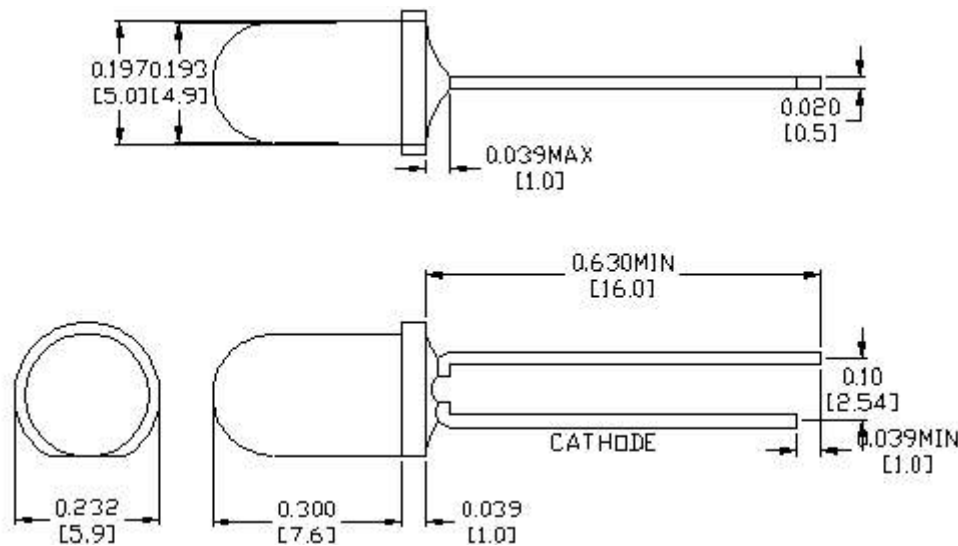


DESCRIPTION

This is a high speed Silicon detector optimized for applications requiring high Responsivity and a fast response time.

FEATURES

- High Responsivity
- High Electrical Bandwidth/Fast response time
- 5 mm Plastic Package



ABSOLUTE MAXIMUM RATINGS

- Storage temperature..... -20°C to +85°C
- Case operating temperature..... 0°C to +70°C
- Lead solder temperature..... 260°C, 10 seconds
- Reverse Breakdown Voltage..... 35 Volts

OUTLINE DIMENSIONS

Tolerances are +/-0.005 inches, except as noted
The case is electrically isolated from the pins.

PARAMETER	TEST CONDITION	SYMBOL	MIN	TYP	MAX	UNIT
Capacitance	V _r = 10 V, f = 1 MHz	C		3.0		pF
Open Circuit Voltage	H = 5.0 mW/cm ²	V _{OC}		400		mV
Short Circuit Current	H = 5.0 mW/cm ²	I _{SC}		2		μA
Dark Current	V _r = 10 Volts, H = 0 mW	I _d		2	10	nA
Response Time	10%-90%, V _r = 10 Volts R _L = 1K Ω	t _r t _f		6.0 6.0		nsec nsec
Peak Wavelength		λ		940		nm
Electrical Bandwidth	V _r = 5 Volts	BWE		50		MHz
Reverse Light Current	H=5.0 mW/cm ² , V _r =5 V	I _L		3.5		μA
Viewing Angle		2 θ1/2		35		Deg

ELECTRO-OPTICAL CHARACTERISTICS (Case T = 25°C)

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